

Amendments to the Claims:

The following listing replaces all prior listing of claims in the application.

Listing of Claims:

CLAIMS

1. Method of fabricating a stacked structure, ~~characterized in that it comprises the following steps comprising:~~
 - a) selecting a first plate (1) and a second plate (5) ~~are selected~~ such that a portion of at least one of said the first (1) and second (5) plates has a ~~[""]structured[""]~~ surface (2; 7), at least in part,
 - b) producing a sacrificial layer (3; 8) ~~is produced~~ on at least a portion of the structured surface (2) of the first plate and/or the structured surface (7) of the second plate (5), and
 - c) bonding the two plates (1; 5) ~~are bonded~~ together.
2. The method according to claim 1 wherein producing the sacrificial layer comprises producing at least a portion of the structured surface of the first plate and at least a portion of the structured surface of the second plate.
- ~~3. 2. The M~~ method according to claim 1, characterized in that wherein selecting a first plate and a second plate comprises selecting plates having predetermined said surface (2; 7) is structured by reason of its physical-chemical properties nature.
- ~~4. 3. The M~~ method according to claim 1, characterized in that wherein selecting comprises selecting said the surface (2; 7) is structured by reason of having a roughness ($r'_{2, r'_{7}}$) greater than a predetermined threshold.
- ~~5. 4. The M~~ method according to claim 43, characterized in that wherein selecting further comprises selecting the structured surface wherein said the predetermined threshold is equal to approximately 0.2 nm root-mean-square (RMS).

~~6.5. The Mmethod according to any one of the preceding claims 1, characterized in that wherein selecting comprises selecting at least one of said the plates (1; 5) that initially has includes a surface layer (6; 9).~~

~~7. 6. The Mmethod according to claim 65, characterized in that wherein selecting further comprises selecting at least one of the plates wherein said the surface layer (6; 9) is comprises a monocrystalline surface layer.~~

~~8. 7. The Mmethod according to claim 6 5 or claim 6, characterized in that wherein selecting further comprises selecting at least one of the plates wherein said the surface layer (6; 9) is of comprises silicon.~~

~~9. 8. The Mmethod according to claim 6 5, further comprising structuring the surface by forming the surface layer having predetermined -characterized in that said surface layer (6; 9) has the effect of structuring said surface (2; 7) because of the physical-chemical nature of that surface layer (6; 9) properties.~~

~~10. The method according to claim 9 where structuring the surface comprises structuring the surface because of a physical-chemical property of that surface layer.~~

~~11. 9. The Mmethod according to claim 9 8, characterized in that wherein forming said the surface layer (6; 9) is of comprises forming a layer of silicon nitride.~~

~~12. 10. The Mmethod according to any one of the preceding claims 1, characterized in that further comprising in that smoothing at least one of the a free surface (4; 10) of the sacrificial layer (3; 8) and/or the a free surface of at least one of said the plates (1; 5) is smoothed before said the step e) bonding.~~

~~13. The method according to claim 1 further comprising smoothing the free surface of the sacrificial layer and the free surface of at least one of the plates before the step e) bonding.~~

~~14. 11. The Mmethod according to any one of claims 1 to 10, characterized in that wherein the said bonding of said step e) is comprises molecular bonding.~~

15. 12. The Mmethod according to any one of claims 1 to 10, characterized in that wherein the bonding of said step e) uses comprises bonding with a sacrificial bonding agent.

16. 13. The Mmethod according to any one of the preceding claims 1, characterized in that wherein the bonding of said step e) further comprises bonding assisted is assisted by at least one of a mechanical means and/or, a plasma treatment, and/or a thermal treatment, these operations being carried out before or during bonding, in a special atmosphere or in the open air.

17. The method according to claim 1 wherein the method further comprises applying a selected atmosphere before bonding.

18. The method according to claim 16 wherein assisting further comprises applying a selected atmosphere during bonding.

19. The method according to claim 16 wherein bonding further comprises exposing the two plates to an open air environment before bonding.

20. The method according to claim 16 wherein bonding further comprises bonding in an open air environment.

21. 14. The Mmethod according to any one of the preceding claims 1, characterized further comprising thinning in that at least one of the two first or second plates (1) and/or (5) is thinned after said step e) bonding.

22. 15. The Mmethod according to any one of the preceding claims 1, characterized in that wherein the a massive major portion of at least one of the plates (1; 5) consists of comprises a semiconductor material.

23. 16. The Mmethod according to claim 15 22, characterized in that wherein said the massive major portion consists of comprises silicon.

24. ~~17.~~ The Method according to ~~any one of claims 1 to 16,~~ characterized in that wherein the sacrificial layer (3; 8) ~~consists of~~ comprises silicon oxide.

25. ~~18.~~ The Method according to ~~any one of claims 1 to 16,~~ characterized in that wherein ~~said material constituting~~ the sacrificial layer (3; 8) is comprises a polymer.

26. ~~19.~~ A Sstacked structure (100), ~~characterized in that it is fabricated by means of a method according to any one of claims 1 to 18.~~

27. ~~20.~~ A Sstacked structure (100), ~~characterized in that it comprises~~ ing a sacrificial layer (3; 8) between a first substrate (1) and a second substrate (5) and in that wherein at least a portion of at least one of said the first (1) and or second (5) substrates has comprises a [""]structured[""] surface (2; 7), at least in part.

28. ~~21.~~ The Sstacked structure according to claim 270, ~~characterized in that~~ wherein said the structured surface (2; 7) is structured by reason of its comprises a surface having predetermined physical-chemical nature properties.

29. ~~22.~~ The Sstacked structure according to claim 270, ~~characterized in that~~ wherein said structuring of the structured surface (2; 7) consists in comprises a surface having a roughness (r'_{z1}, r'_{z2}) greater than a predetermined threshold.

30. ~~23.~~ The Sstacked structure according to claim 292, ~~characterized in that~~ wherein said the predetermined threshold is equal to approximately 0.2 nm.

31. ~~24.~~ The Sstacked structure according to ~~any one of claims 270 to 23,~~ characterized in that wherein at least one of said the first or second substrates (1; 5) has a surface layer (6; 9).

32. ~~25.~~ The Sstacked structure according to claim 2431, ~~characterized in that~~ wherein said the surface layer (6; 9) is comprises a monocrystalline surface layer.

33. ~~26.~~ The Sstacked structure according to claim 2431 ~~or claim 25,~~ characterized in that wherein said the surface layer (6; 9) consists of comprises silicon.

34. ~~27.~~ The Sstacked structure according to claim ~~24~~31, characterized in that wherein said the surface layer (6; 9) ~~has the effect of structuring said surface (2; 7) by reason of the~~ comprises a material having predetermined physical-chemical properties nature of that surface layer (6; 9).

35. ~~28.~~ The Sstacked structure according to claim ~~27~~34, characterized in that wherein said the surface layer (6; 9) ~~consists of~~ comprises silicon nitride.

36. ~~29.~~ The Sstacked structure according to ~~any one of claims 20~~7 ~~to 28~~, characterized in that wherein the a massive major portion of at least one of the first or second substrates (1; 5) ~~consists of~~ comprises a semiconductor material.

37. ~~30.~~ The Sstacked structure according to claim ~~29~~36, characterized in that wherein said the massive major portion ~~consists of~~ comprises silicon.

38. ~~31.~~ The Sstacked structure according to ~~any one of claims 27~~0 ~~to 30~~, characterized in that wherein the sacrificial layer (3; 8) ~~consists of~~ comprises silicon oxide.

39. ~~32.~~ The Sstacked structure according to ~~any one of claims 27~~0 ~~to 30~~, characterized in that wherein the material constituting the sacrificial layer (3; 8) is comprises a polymer.

40. ~~33.~~ The Sstacked structure according to ~~any one of claims 27~~0 ~~to 32~~, characterized in that wherein at least one of said the first or second substrates (1; 5) is comprises a thin layer.